



BM75100BG

100V, 10A⁽¹⁾, TBR series Schottky

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	1909 μm	75 mil
	Top Metal Pad Size (B)	1724 μm	68 mil
	Passivation Seal (C)	1829 μm	72 mil
	Wafer Thickness (D)	254±15 μm	10±0.6 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Diameter	6 inch	
	Gross Die	4233	
	Top Side Metallization/ Layer Thickness	Ag / 3 ±0.3 μm	
	Back Side Metallization/ Layer Thickness	Ag / 2 ±0.2 μm	
	Recommended Storage Environment	Store in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C±3°C)	

Electrical Characteristics in C/P test (T_J =25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{BR}	Reverse Breakdown Voltage	100	—	—	V	I _R =300μA
V _F	Instantaneous Forward Voltage	—	0.50	0.54	V	I _F =3A ⁽²⁾
		—	0.72	0.77	V	I _F =10A ⁽²⁾
I _R	Reverse Leakage Current	—	18.5	30	μA	V _R =100V
T _J , T _{STG}	Operating and Storage Temperature	-40°C to 150°C Max				